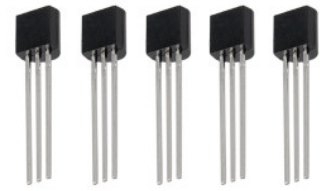




**PRODUCT NAME** : 2N4126 PNP General Purpose Transistor

**PRICE** : Rs 20.00

**SKU** : RM2058



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## DESCRIPTION

## Features

- Collector-Emitter Volt ( $V_{ce0}$ ): 25V
- Collector-Base Volt ( $V_{cb0}$ ): 25V
- Collector Current ( $I_c$ ): 0.3A
- $h_{fe}$ : 120-360 @ 2mA
- Power Dissipation ( $P_{tot}$ ): 500mW
- Current-Gain-Bandwidth ( $f_{total}$ ): 250MHz
- Type: PNP

**PNP general purpose transistor**

**2N4126**

**FEATURES**

- Low current (max. 200 mA)
- Low voltage (max. 25 V).

**APPLICATIONS**

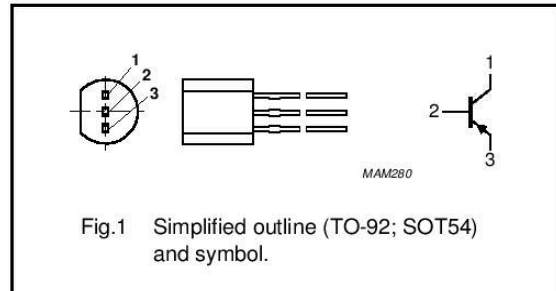
- General purpose switching and amplification, e.g. small-signal audio-frequency applications.

**DESCRIPTION**

PNP transistor in a TO-92; SOT54 plastic package. NPN complement: 2N4124.

**PINNING**

PIN	DESCRIPTION
1	collector
2	base
3	emitter



**QUICK REFERENCE DATA**

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	–25	V
$V_{CEO}$	collector-emitter voltage	open base	–	–25	V
$I_{CM}$	peak collector current		–	–300	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$	–	500	mW
$h_{FE}$	DC current gain	$I_C = -2\text{ mA}; V_{CE} = -1\text{ V}$	120	360	
$f_T$	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -20\text{ V}; f = 100\text{ MHz}$	250	–	MHz

**PNP general purpose transistor**

**2N4126**

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	–25	V
$V_{CEO}$	collector-emitter voltage	open base	–	–25	V
$V_{EBO}$	emitter-base voltage	open collector	–	–4	V
$I_C$	collector current (DC)		–	–200	mA
$I_{CM}$	peak collector current		–	–300	mA
$I_{BM}$	peak base current		–	–100	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; note 1	–	500	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C
$T_{amb}$	operating ambient temperature		–65	+150	°C

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	250	K/W

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

**CHARACTERISTICS**

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0$ ; $V_{CB} = -20\text{ V}$	–	–50	nA
$I_{EBO}$	emitter cut-off current	$I_C = 0$ ; $V_{EB} = -3\text{ V}$	–	–50	nA
$h_{FE}$	DC current gain	$I_C = -2\text{ mA}$ ; $V_{CE} = -1\text{ V}$ ; note 1	120	360	
		$I_C = -50\text{ mA}$ ; $V_{CE} = -1\text{ V}$ ; note 1	60	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -50\text{ mA}$ ; $I_B = -5\text{ mA}$ ; note 1	–	–400	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -50\text{ mA}$ ; $I_B = -5\text{ mA}$ ; note 1	–	–950	mV
$C_c$	collector capacitance	$I_E = I_e = 0$ ; $V_{CB} = -5\text{ V}$ ; $f = 1\text{ MHz}$	–	4.5	pF
$C_e$	emitter capacitance	$I_C = I_c = 0$ ; $V_{EB} = -0.5\text{ V}$ ; $f = 1\text{ MHz}$	–	10	pF
$f_T$	transition frequency	$I_C = -10\text{ mA}$ ; $V_{CE} = -20\text{ V}$ ; $f = 100\text{ MHz}$	250	–	MHz
F	noise figure	$I_C = -100\text{ }\mu\text{A}$ ; $V_{CE} = -5\text{ V}$ ; $R_S = 1\text{ k}\Omega$ ; $f = 10\text{ Hz to }15.7\text{ kHz}$	–	4	dB

**Note**

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$ .

